

AMENDMENT TO THE CLAIMS

1-11. (Cancelled)

12. (New) A semiconductor device comprising:
- an insulating film;
- an interconnect made of a first conductive film and a second conductive film that are stacked in sequence from the interconnect underside on the insulating film;
- on the insulating film, a capacitor composed of:
- a lower capacitor electrode made of the first conductive film;
- a dielectric film formed on the lower capacitor electrode; and
- an upper capacitor electrode made of the second conductive film and formed on the dielectric film,
- wherein each of the lower capacitor electrode, the dielectric film, and the upper capacitor electrode has a same pattern; and
- lower contacts are formed in the insulating film on the bottom surface of the lower capacitor electrode, the lower contacts being connected to the lower capacitor electrode.
13. (New) The semiconductor device of Claim 12, wherein
- a lower insulating film is formed beneath the insulating film;
- a lower interconnect is formed on the lower insulating film; and
- the lower contacts are connected to the lower interconnect.

14. (New) The semiconductor device of Claim 12, wherein a surface of the insulating film on which the capacitor is formed is planarized.

15. (New) The semiconductor device of Claim 13, wherein an upper insulating film is formed so as to cover the capacitor and the interconnect; and upper contacts are formed in the upper insulating film on the upper surface of the upper capacitor electrode, the upper contacts being connected to the upper capacitor electrode.

16. (New) The semiconductor device of Claim 15, wherein an upper interconnect is formed on the upper insulating film; and the upper contacts are connected with the upper interconnect.

17. (New) The semiconductor device of Claim 12, wherein the first conductive film is made of a metal nitride.

18. (New) The semiconductor device of Claim 17, wherein the dielectric film is SiN.

19. (New) The semiconductor device of Claim 18, wherein the second conductive film is made of an aluminum alloy.